Tomohiro Yamaguchi

List of Publications by Year
in descending order

31	887	1307594 7	713466 21
papers	citations	h-index	g-index

31	31	31	1039
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Effect of thermal annealing on photoexcited carriers in nitrogen-ion-implanted Î²-Ga2O3 crystals detected by photocurrent measurement. AIP Advances, 2021, 11, .	1.3	3
2	Selective observation of transverse optical phonons of Au modes to evaluate free charge carrier parameters in Î²-Ga2O3 substrate and homoepitaxial film. Applied Physics Letters, 2021, 118, 252101.	3.3	0
3	Identification of free and bound exciton emission of MgO single crystal in vacuum ultraviolet spectral range. Applied Physics Letters, 2021, 119, .	3.3	7
4	Photoelectron spectroscopic study on electronic state of corundum In2O3 epitaxial thin film grown by mist-CVD. Japanese Journal of Applied Physics, 2020, 59, SIIG12.	1.5	4
5	Impact of hydrochloric acid on the epitaxial growth of In₂O₃ films on (0001)Î±-Al₂O₃ substrates by mist CVD. Applied Physics Express, 2020, 13, 075504.	2.4	6
6	Epitaxial mist chemical vapor deposition growth and characterization of Cu3N films on (0001)Î±-Al2O3 substrates. Applied Physics Express, 2020, 13, 075505.	2.4	1
7	MOCVD Growth and Investigation of InGaN/GaN Heterostructure Grown on AlGaN/GaN-on-Si Template. Applied Sciences (Switzerland), 2019, 9, 1746.	2.5	4
8	In Situ Synchrotron X-ray Diffraction Reciprocal Space Mapping Measurements in the RF-MBE Growth of GaInN on GaN and InN. Crystals, 2019, 9, 631.	2.2	5
9	Observation of Electroreflectance Spectra of eta-Ga2O3 Single Crystal. , 2019, , .		0
10	Relation Between Electrical and Optical Properties of pâ€Type NiO Films. Physica Status Solidi (B): Basic Research, 2018, 255, 1700311.	1.5	13
11	Surface and bulk electronic structures of unintentionally and Mg-doped In0.7Ga0.3N epilayer by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2018, 123, 095701.	2.5	1
12	Structural evaluation of ions-implanted GaN films by photothermal deflection spectroscopy. AIP Advances, 2018, 8, .	1.3	15
13	Fabrication of Ag dispersed ZnO films by molecular precursor method and application in GaInN blue LED. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600598.	1.8	1
14	Surface and bulk electronic structures of heavily Mg-doped InN epilayer by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2017, 121, .	2.5	5
15	Surface plasmon resonant emission from Ag dispersed ZnO films fabricated by molecular precursor method. , 2016, , .		0
16	Spectroscopic ellipsometry studies on Î²-Ga₂O₃films and single crystal. Japanese Journal of Applied Physics, 2016, 55, 1202B2.	1.5	33
17	Nitride-MBE system for in situ synchrotron X-ray measurements. Japanese Journal of Applied Physics, 2016, 55, 05FB05.	1.5	8
18	Growth of rocksalt-structured Mg_xZn_{1â^'} _xO (x > 0.5) films on MgO substrates and their deep-ultraviolet luminescence. Applied Physics Express, 2016, 9, 111102.	2.4	26

#	Article	IF	Citations
19	Optical properties of Ga_{0.82}In_{0.18}N p-n homojunction blue-green light-emitting-diode grown by radio-frequency plasma-assisted molecular beam epitaxy. Transactions of the Materials Research Society of Japan, 2015, 40, 149-152.	0.2	0
20	Valence band ordering in Î²-Ga₂O₃studied by polarized transmittance and reflectance spectroscopy. Japanese Journal of Applied Physics, 2015, 54, 112601.	1.5	261
21	Systematic investigation of surface and bulk electronic structure of undoped In-polar InN epilayers by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2013, 114, .	2.5	17
22	GaN growth on (111)Al substrates by CSâ€MBE and their chemical liftâ€off technique. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 385-387.	0.8	0
23	Electronâ€beam incidentâ€angleâ€resolved cathodoluminescence studies on bulk ZnO crystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 869-872.	0.8	6
24	Effect of (GaN/AlN) alternatingâ€sourceâ€feeding buffer layer in GaN growth on Al₂O₃ and silicon by RFâ€MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1549-1552.	0.8	2
25	The strain-controlled GaN growth on Si by RF-MBE. , 2012, , .		0
26	Fabrication of a-plane InN nanostructures on patterned a-plane GaN template by ECR-MBE. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 447-450.	1.8	2
27	RF-Molecular Beam Epitaxy Growth and Properties of InN and Related Alloys. Japanese Journal of Applied Physics, 2003, 42, 2549-2559.	1.5	394
28	Indium Droplet Elimination by Radical Beam Irradiation for Reproducible and High-Quality Growth of InN by RF Molecular Beam Epitaxy. Applied Physics Express, 0, 2, 051001.	2.4	68
29	Mist Chemical Vapor Deposition Growth of Î±â€In 2 O 3 Films Using Indium Oxide Powder as Source Precursor. Physica Status Solidi (B): Basic Research, 0, , 2100414.	1.5	3
30	Plasma excited molecular beam epitaxyï¼proposal and achievements through R&D of compound semiconductor materials and devicesï¼. Japanese Journal of Applied Physics, 0, , .	1.5	1
31	VUV emission properties of rocksaltâ€structured MgZnO microcrystals prepared on quartz glass substrates. Physica Status Solidi (B): Basic Research, 0, , 2100354.	1.5	1